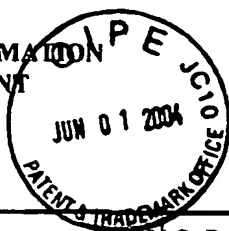


FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-012DV

APPLICANTS: Lee *et al.*

SERIAL NO.: 10/788,741

FILING DATE: February 27, 2004

GROUP: 2811

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A73	5,951,757	09/14/1999	Dubbelday <i>et al.</i>			
TN	A74	6,461,945	10/08/2002	Yu			

FOREIGN PATENT DOCUMENTS

EXAM INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

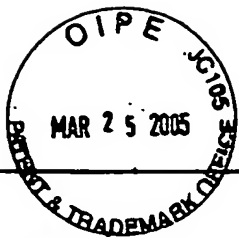
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								

EXAMINER

T. NEMEN

DATE CONSIDERED

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SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANT(S): Lee *et al.*

SERIAL NO.: 10/788,741

FILING DATE: February 27, 2004

GROUP: 2813

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A75	2002/0063292	05/30/2002	Armstrong <i>et al.</i>			
	A76	2002/0190284	12/19/2002	Murthy <i>et al.</i>			
	A77	2004/0007724	01/15/2004	Murthy <i>et al.</i>			
	A78	2004/0014276	01/22/2004	Murthy <i>et al.</i>			
	A79	2004/0070035	04/15/2004	Murthy <i>et al.</i>			
	A80	2004/0084735	05/06/2004	Murthy <i>et al.</i>			
	A81	2004/0119101	06/24/2004	Schrom <i>et al.</i>			
	A82	2004/0142545	07/22/2004	Ngo <i>et al.</i>			
	A83	2004/0173815	09/09/2004	Yeo <i>et al.</i>			
	A84	5,089,872	02/18/1992	Ozturk <i>et al.</i>			
	A85	5,242,847	09/07/1993	Ozturk <i>et al.</i>			
	A86	6,228,694	05/08/2001	Doyle <i>et al.</i>			
	A87	6,235,568	05/22/2001	Murthy <i>et al.</i>			
	A88	6,281,532	08/28/2001	Doyle <i>et al.</i>			
	A89	6,326,664	12/04/2001	Chau <i>et al.</i>			
	A90	6,563,152	05/13/2003	Roberds <i>et al.</i>			
	A91	6,605,498	08/12/2003	Murthy <i>et al.</i>			
	A92	6,621,131	09/16/2003	Murthy <i>et al.</i>			
	A93	6,657,223	12/02/2003	Wang <i>et al.</i>			
	A94	6,703,648	03/09/2004	Xiang <i>et al.</i>			
✓	A95	6,743,684	06/01/2004	Liu			

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FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-012DV					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Lee <i>et al.</i>					
				SERIAL NO.: 10/788,741					
				FILING DATE: February 27, 2004					
				GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C75	Gannavaram, <i>et al.</i> , "Low Temperature ($\leq 800^{\circ}\text{C}$) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> , (2000), pp. 437-440.							
TN	C76	Ge <i>et al.</i> , "Process-Strained Si (PSS) CMOS Technology Featuring 3D Strain Engineering," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2003) pp. 73-76.							
TN	C77	Ghani <i>et al.</i> , "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2003), 978-980.							
TN	C78	Hamada <i>et al.</i> , "A New Aspect of Mechanical Stress Effects in Scaled MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 4 (April 1991), pp. 895-900.							
TN	C79	Huang <i>et al.</i> , "Isolation Process Dependence of Channel Mobility in Thin-Film SOI Devices," <u>IEEE Electron Device Letters</u> , Vol. 17, No. 6 (June 1996), pp. 291-293.							
TN	C80	Huang <i>et al.</i> , "LOCOS-Induced Stress Effects on Thin-Film SOI Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 44, No. 4 (April 1997), pp. 646-650.							
TN	C81	Huang, <i>et al.</i> , "Reduction of Source/Drain Series Resistance and Its Impact on Device Performance for PMOS Transistors with Raised $\text{Si}_{1-x}\text{Ge}_x$ Source/Drain", <u>IEEE Electron Device Letters</u> , Vol. 21, No. 9, (Sept. 2000) pp. 448-450.							
TN	C82	Iida <i>et al.</i> , "Thermal behavior of residual strain in silicon-on-insulator bonded wafer and effects on electron mobility," <u>Solid-State Electronics</u> , Vol. 43 (1999), pp. 1117-1120.							
EXAMINER		T. NGUYEN			DATE CONSIDERED			6/22/06	

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-012DV APPLICANT(S): Lee <i>et al.</i> SERIAL NO.: 10/788,741 FILING DATE: February 27, 2004 GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
TN	C83	Ito <i>et al.</i> , "Mechanical Stress Effect on Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2000), pp. 247-250.							
TN	C84	Lochtefeld <i>et al.</i> , "Investigating the Relationship Between Electron Mobility and Velocity in Deeply Scaled NMOS via Mechanical Stress," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 12 (2001), pp. 591-593.							
TN	C85	Ootsuka <i>et al.</i> , "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Applications," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2000), pp. 575-578.							
TN	C86	Ota <i>et al.</i> , "Novel Locally Strained Channel Technique for High Performance 55nm CMOS," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2002), pp. 27-30.							
TN	C87	Öztürk, <i>et al.</i> , "Advanced Si _{1-x} Ge _x Source/Drain and Contact Technologies for Sub-70 nm CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> , (2002), pp. 375-378.							
TN	C88	Öztürk, <i>et al.</i> , "Low Resistivity Nickel Germanosilicide Contacts to Ultra-Shallow Si _{1-x} Ge _x Source/Drain Junctions for Nanoscale CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> (2003), pp. 497-500.							
TN	C89	Öztürk, <i>et al.</i> , "Selective Silicon-Germanium Source/Drain Technology for Nanoscale CMOS," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 717, (2002), pp. C4.1.1-C4.1.12.							
TN	C90	Öztürk, <i>et al.</i> , "Ultra-Shallow Source/Drain Junctions for Nanoscale CMOS Using Selective Silicon-Germanium Technology," <u>Extended Abstracts of International Workshop on Junction Technology</u> , (2001), pp. 77-82.							
EXAMINER		T. NGUYEN				DATE CONSIDERED 6/22/06			

FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-012DV					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Lee et al.					
				SERIAL NO.: 10/788,741					
				FILING DATE: February 27, 2004					
				GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
TN	C91	Shimizu <i>et al.</i> , "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2001), pp. 433-436.							
TN	C92	Thompson <i>et al.</i> , "A Logic Nanotechnology Featuring Strained-Silicon," <u>IEEE Electron Device Letters</u> , Vol. 25, No. 4 (April 2004), pp. 191-193.							
TN	C93	Thompson <i>et al.</i> , "A 90 nm Logic Technology Featuring 50nm Strained-Silicon Channel Transistors, 7 layers of Cu Interconnects, Low k ILD, and 1um ² SRAM Cell," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2002), pp. 61-64.							
TN	C94	Tiwari <i>et al.</i> , "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (1997), pp. 939-941.							
TN	C95	Uchino, <i>et al.</i> , "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-μm CMOS ULSIs," <u>IEEE International Electron Device Meeting Technical Digest</u> , (1997), pp. 479-482.							
EXAMINER		T. N. NGUYEN			DATE CONSIDERED 6/22/06				

FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-012DV
INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/ 788 741
	FILING DATE: Herewith 2-27-04 GROUP: Not yet assigned

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A1	4,710,788	12/01/1987	Dämbkes et al.			
TN	A2	4,990,979	02/05/1991	Otto			
TN	A3	5,241,197	08/31/1993	Murakami et al.			
TN	A4	5,291,439	03/01/1994	Kauffmann et al.			
TN	A5	5,442,205	08/15/1995	Brasen et al.			
TN	A6	5,523,592	06/04/1996	Nakagawa et al.			
TN	A7	5,534,713	07/09/1996	Ismail et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
TN	B1	41 01 167 A1	07/23/1992	DE				No	Yes (abstract only)
TN	B2	4-307974	10/30/1992	JP				No	No
TN	B3	7-106446	04/21/1995	JP				No	No
TN	B4	0 683 522 A2	11/22/1995	EP				No	Yes
TN	B5	0 829 908 A2	03/18/1998	EP				No	Yes

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
TN	C1	Meyerson et al., "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988) pp. 2555-2557.
TN	C2	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.
TN	C3	Robbins et al., "A model for heterogeneous growth of Si _{1-x} Ge _x films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991) pp. 3729-3732.
TN	C4	"2 Bit/Cell EEPROM Cell Using Band-to-Band Tunneling for Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , Vol. 35, No. 4B (September 1992) pp. 136-140.
TN	C5	Wesler et al., "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," <u>Electron Devices Meeting, 1992. Technical Digest</u> (December 13, 1992) pp. 31.7.1-31.7.3.
TN	C6	Grützmacher et al., "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993) pp. 2531-2533.
EXAMINER J. N. GRIFFIN		DATE CONSIDERED 6/22/06

FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-012DV
INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/788741 2-27-04
	FILING DATE: Herewith GROUP: Not yet assigned

U.S. PATENT DOCUMENTS

EXAM INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A8	5,596,527	01/12/1997	Tomioka et al.	—	—	
TN	A9	5,617,351	04/01/1997	Bertin et al.	—	—	
TN	A10	5,683,934	11/04/1997	Candelaria	—	—	
TN	A11	5,739,567	04/14/1998	Wong	—	—	
TN	A12	5,777,347	07/07/1998	Bartelink	—	—	
TN	A13	5,786,612	07/28/1998	Otani et al.	—	—	
TN	A14	5,792,679	08/11/1998	Nakato	—	—	
TN	A15	5,808,344	09/15/1998	Ismail et al.	—	—	
TN	A16	5,891,769	04/06/1999	Liaw et al.	—	—	
TN	A17	5,906,951	05/25/1999	Chu et al.	—	—	
TN	A18	5,998,807	12/07/1999	Lustig et al.	—	—	

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EXAM. INT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>TN</i>	B6	0 838 858 A2	04/29/1998	EP	_____	_____		No	Yes
<i>TN</i>	B7	11-233744	08/27/1999	JP	_____	_____		No	No
<i>TN</i>	B8	WO 98/59365	12/30/1998	PCT	_____	_____		No	Yes
<i>TN</i>	B9	WO 99/53539	10/21/1999	PCT	_____	_____		No	Yes
<i>TN</i>	B10	2001319935	05/2000	JP	_____	_____		Yes	No

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
TN	C7	Welser et al., "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>Electron Devices meetings, 1993, Technical Digest</u> (December 1993) pp. 21.3.1-21.3.4.
TN	C8	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.
TN	C9	Tweet et al., "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994) pp. 2579-2581.
EXAMINER	T. N. HUIJEN	DATE CONSIDERED 6/22/06

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-012DV APPLICANTS: Lee et al. SERIAL NO.: Not yet assigned 10/788741 FILING DATE: Herewith 2/27/04 GROUP: Not yet assigned				
U.S. PATENT DOCUMENTS								
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
TN	A19	6,013,134	01/11/2000	Chu et al.				
TN	A20	6,058,044	05/02/2000	Sugiura et al.				
TN	A21	6,059,895	05/09/2000	Chu et al.				
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EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
TN	B11	1 020 900 A2	07/19/2000	EP			No	Yes
TN	B12	WO 00/54338	09/14/2000	PCT			No	Yes
TN	B13	WO 01/54202 A1	07/26/2001	PCT			No	Yes
TN	B14	WO 01/93338 A1	12/06/2001	PCT			No	Yes
TN	B15	WO 01/99169 A2	12/27/2001	PCT			No	Yes
TN	B16	1 174 928 A1	01/23/2002	EP			No	Yes
OTHER ART, JOURNAL ARTICLES, ETC.								
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
TN	C10	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest</u> (1995) pp. 761-764.						
TN	C11	König et al., "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995) pp. 1595-1602.						
TN	C12	Rim et al., "Enhanced Hole Mobilities in Surface-Channel Strained-Si p-MOSFETs," <u>Solid State Electronics Laboratory, Stanford University, Stanford, CA 94305</u> (1995) pp. 20.3.1-20.3.4.						
TN	C13	Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University (1995) pp. 1-205.						
TN	C14	Sadek et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 8 (August 1996) pp. 1224-1232.						
TN	C15	Nayak et al., "High Mobility Strained-Si PMOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996) pp. 1709-1716.						
TN	C16	Schäffler, "High-mobility Si and Ge structures," <u>Semicond. Sci. Technol.</u> , Vol. 12 (1997) pp. 1515-1549.						
TN	C17	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semicon. Sci. Technol.</u> (1997) (abstract).						
EXAMINER <i>T. N. NUNEN</i>				DATE CONSIDERED <i>6/22/06</i>				

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INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: Not yet assigned 10/788741

FILING DATE: 2-27-04 Herewith GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A22	6,096,590	08/01/2000	Chan et al.			
TN	A23	6,107,653	08/22/2000	Fitzgerald			
TN	A24	6,111,267	08/29/2000	Fischer et al.			
TN	A25	6,117,750	09/12/2000	Bensahel et al.			
TN	A26	6,130,453	10/10/2000	Mei et al.			
TN	A27	6,143,636	11/07/2000	Forbes et al.			
TN	A28	6,204,529	03/20/2001	Lung et al.			
TN	A29	6,207,977 B1	03/27/2001	Augusto			
TN	A30	US 2001/0003364 A1	06/14/2001	Sugawara et al.			
TN	A31	6,249,022	06/19/2001	Lin et al.			
TN	A32	6,251,755 B1	06/26/2001	Furukawa et al.			
TN	A33	6,266,278	07/24/2001	Harari et al.			
TN	A34	US 2002/0100942 A1	08/01/2001	Fitzgerald et al.			
TN	A35	6,339,232 B1	01/15/2002	Takagi			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
TN	B17	WO 02/15244A2	02/21/2002	PCT				No	Yes
TN	B18	WO 02/13262 A2	02/14/2002	PCT				No	Yes
TN	B19	WO 02/47168 A2	06/13/2002	PCT				No	Yes
TN	B20	WO 02/071488 A1	09/12/2002	PCT				No	Yes
TN	B21	WO 02/071491 A1	09/12/2002	PCT				No	Yes

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
TN	C18	König et al., "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.							
TN	C19	Höck et al., "Carrier mobilities in modulation doped Si _{1-x} Ge _x heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998) pp. 141-144.							

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DATE CONSIDERED

6/22/06

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>TN</i>	A36	6,350,993 B1	02/26/2002	Chu et al.			
<i>TN</i>	A37	US 2002/0125471 A1	09/12/2002	Fitzgerald et al.			12/04/2001
<i>TN</i>	A38	US 2002/140031 A1	10/03/2002	Rim			03/31/2001
<i>TN</i>	A39	US 2002/0125497 A1	09/12/2002	Fitzgerald			07/16/2001

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>TN</i>	B22	WO 02/071495 A1	09/12/2002	PCT				No	Yes

OTHER ART, JOURNAL ARTICLES, ETC.

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<i>TN</i>	C20	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semicond. Sci. Technol.</u> , Vol. 13 (1998) pp. 1225-1246.							
<i>TN</i>	C21	Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201 (1999) pp. 734-738							
<i>TN</i>	C22	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Submitted to the Massachusetts Institute of Technology Department of Electrical Engineering and Computer Science on June 30, 1999, pp. 1-154.							
<i>TN</i>	C23	O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETS," <u>Semicond. Sci. Technol.</u> , Vol. 14 (1999) pp. 784-789.							
<i>TN</i>	C24	Rim, "Application of Silicon Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University (July 1999) pp. 1-184							
<i>TN</i>	C25	Parker et al., "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43, No. 8, (August 1999) pp. 1497-1506.							
EXAMINER		<i>T. N. KUMAR</i>			DATE CONSIDERED		<i>6/22/06</i>		

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INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: Not yet assigned

FILING DATE: ~~Herewith~~

GROUP: Not yet assigned

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TN	C26	Xie, "SiGe Field effect transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999) pp. 89-121.						
TN	C27	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> Vol. 369, No. 1-2 (2000) pp. 148-151.						
TN	C28	Herzog et al., "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> Vol. 380 (2000) pp. 36-41.						
TN	C29	Mizuno et al., "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE Electron Device Letters</u> Vol. 21, No. 5 (May 2000) pp. 230-232.						
TN	C30	Höck et al., "High hole mobility in Si _{0.17} Ge _{0.83} channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Volume 76, No. 26 (June 26, 2000) pp. 3920-3922.						
TN	C31	Rim et al., "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's," <u>IEEE Transactions on Electron Devices</u> Vol. 47, No. 7 (July 2000) pp. 1406-1415.						
TN	C32	Barradas et al., "RBS analysis of MBE-grown Si/Ge(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> (2001) (abstract).						
TN	C33	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Volume 30, No. 12 (2001) pp. L37-L39						
TN	C34	Lee et al., "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si _{1-x} Ge _x /Si virtual substrates," <u>Applied Physics Letters</u> , Volume 79, No. 20 (November 12, 2001) pp. 3344-3346.						
TN	C35	Leitz et al., "Hole mobility enhancements in strained Si/Si _{1-x} Ge _x p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si _{1-x} Ge _x (x<y) virtual substrates," <u>Applied Physics Letters</u> , Volume 79, No. 25 (December 17, 2001) pp. 4246-4248.						
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6/22/06

FORM PTO - 1449

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ATTORNEY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: Not yet assigned

FILING DATE: ~~Herewith~~ 2-27-04 GROUP: Not yet assigned

10/788741

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TDV	C37	Lee et al., "Strained Ge channel p-type MOSFETs fabricated on Si _{1-x} Ge _x /Si virtual substrates," <u>Mat. Res. Soc. Symp. Proc.</u> , Volume 686 (2002) pp. A1.9.1-A1.9.5.
TN	C38	Leitz et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," <u>Mat. Res. Soc. Symp. Proc.</u> , Volume 686 (2002) pp. A3.10.1-A3.10.6.
TN	C39	Li et al., "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>J. Vac. Sci. Technol.</u> , A 20(3) (May/June 2002) pp. 1030-1033.
EXAMINER	T. NGUYEN	
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FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-012DV
INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/788741
	FILING DATE: ²⁻²⁷⁻⁰⁴ Herewith GROUP: Not yet assigned

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TN	C40	Eaglesham et al., "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990) pp. 1943-1946.
TN	C41	Fitzgerald et al., "Totally relaxed Ge _x Si _{1-x} layers with low threading dislocation densities grown on Si substrates," <u>Appl. Phys. Lett.</u> , Vol. 59, No. 7 (August 12, 1991) pp. 811-813.
TN	C42	Fitzgerald et al., "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>J. Vac. Sci. Technol. B</u> , Volume 10, No. 4 (July/August 1992) pp. 1807-1819.
TN	C43	Xie et al., "Very high mobility two-dimensional hole gas in Si/ Ge _x Si _{1-x} /Ge structures grown by molecular beam epitaxy," <u>Appl. Phys. Lett.</u> , Vol. 63, No. 16 (October 18, 1993) pp. 2263-2264.
TN	C44	Wesler et al., "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994) pp. 100-102.
EXAMINER <i>J. N. SUMNER</i>		DATE CONSIDERED <i>6/22/06</i>

FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-012DV
INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 2-27-04
	FILING DATE: Herewith GROUP: Not yet assigned

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EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

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TN	C46	Xie et al., "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>The Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994) pp. 3006-3009.
TN	C47	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 μ m bulk CMOS Experimental study," <u>IEEE</u> , (1996) pp. 21.2.1-21.2.4.
TN	C48	Kearney et al., "The effect of alloy scattering on the mobility of holes in a Si _{1-x} Ge _x quantum well," <u>Semicond. Sci Technol.</u> , Vol. 13 (1998) pp. 174-180.
TN	C49	Höck et al., "High performance 0.25 μ m p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998) pp. 1888-1889.
EXAMINER	T. N. BROWN	
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INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/788,741
	FILING DATE: Herewith 2-27-04 GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

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TN	C50	Bufler et al., "Hole transport in strained Si _{1-x} Ge _x alloys on Si _{1-y} Ge _y substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
TN	C51	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering B67</u> , (1999) pp. 53-61.
TN	C52	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.
TN	C53	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001) pp. 321-323.
TN	C54	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001) pp. 2730-2736.
TN	C55	Currie et al., "Carrier mobilities and process stability of strained S in- and p-MOSFETs on SiGe virtual substrates," <u>J. Vac. Sci. Technol. B</u> , Vol. 19, No. 6 (Nov/Dec 2001) pp. 2268-2279.
EXAMINER	T. NIKUMEN	
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INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned <i>10/788741</i>
	FILING DATE: <i>2-27-04</i> Herewith GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>TN</i>	A40	6,399,970 B2	06/04/2002	Kubo et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	

EXAMINER	<i>T. NEUMEN</i>	DATE CONSIDERED	<i>6/22/06</i>
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
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TN	C57	König et al., "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993) pp. 205-207.						
TN	C58	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>J. Appl. Phys.</u> , Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.						
TN	C59	Currie et al., "Controlling threading dislocation densities in Ge on Si using graded SiGe layers and chemical-mechanical polishing," <u>Applied Physics Letters</u> , Vol. 72, No. 14 (April 6, 1998) pp 1718-1720.						
TN	C60	Reinking et al., "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999) pp. 503-504.						
TN	C61	Koester et al., "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000) pp. 110-112.						
TN	C62	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High V _{oc} Using Graded GeSi Buffers," <u>IEEE</u> (2000) pp. 1006-1011						
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INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
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	GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A41	5,780,922	07/14/1998	Mishra et al.			
TN	A42	5,986,287	11/16/1999	Eberl et al.			
TN	A43	6,498,359	12/24/2002	Schmidt et al.			05/18/2001

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TN	B23	63122176	05/26/88	JP				Y	Y

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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
TN	C63	Reinking et al., "Fabrication of High-Mobility Ge p-Channel MOSFETs on Si-Substrates," Electronics Letters , Vol. 35, No. 6 (March 18, 1999) pp. 503-504.							
TN	C64	Rosenblad et al., "Virtual Substrates for the n- and p-type Si-MODFET Grown at Very High Rates," <u>Materials Science and Engineering</u> , Vol. B74 (2000) pp. 113-117.							
TN	C65	Ueno et al., "Low Temperature Buffer Growth for Modulation Doped SiGe/Ge/SiGe Heterostructures with High Hole Mobility," <u>Thin Solid Films</u> , Vol. 369 (2000) pp. 320-323.							
TN	C66	Yousif et al., "Recent Critical Issues in Si/Si _{1-x} Ge _x /Si Heterostructure FET Devices," <u>Solid-State Electronics</u> , Vol. 45, No. 11 (2001) pp. 1931-1937.							
TN	C67	Anonymous, "Germanium P-Channel Mosfet," <u>IBM Technical Disclosure Bulletin</u> , Vol. 28, No. 2 (July 1, 1985) p. 500.							
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INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/788741
	FILING DATE: Herewith ²⁻²⁷⁻⁰⁴ GROUP: Not yet assigned

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TN	C68	Aigouy et al., "MOVPE Growth and optical characterization of ZnSe/ZnS strained layer superlattices," <u>Superlattices and Microstructures</u> , Vol. 16, No. 1 (1994) pp. 71-76
TN	C69	Kikkawa et al., "Effect of strained InGaAs step bunching on mobility and device performance in n-InGaP/InGaAs/GaAs pseudomorphic heterostructures grown by metalorganic vapor phase epitaxy," <u>Journal of Crystal Growth</u> , Vol. 145 (1994) pp. 799-807.
TN	C70	Pelekanos et al., "Interface roughness correlation in CdTe/CdZnTe strained quantum wells," <u>Journal of Crystal Growth</u> , Vol. 184/185 (1998) pp. 886-889.
EXAMINER	T. N. BRUMEN	
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	APPLICANTS:	Lee et al.
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	GROUP:	Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A44	5,963,817	10/05/1999	Chu et al.			
	A45	2002/0100942	08/01/2002	Fitzgerald et al.			
	A46	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A47	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A48	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A49	2002/0197803	12/26/2002	Leitz et al.			06/21/2002
	A50	2003/0013323	01/16/2003	Hammond et al.			06/14/2002
↓	A51	2003/0052334	03/20/2003	Lee et al.			06/18/2002

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
TN	B24	02241195	08/28/2002	JP			02/15/2001	NO	YES

OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
EXAMINER	T. NGUYEN	
	DATE CONSIDERED	6/22/06

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INFORMATION DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: ~~Not yet assigned~~ 10/788741

FILING DATE: Herewith 2-27-04

GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A52	2003/0057439	03/27/2003	Fitzgerald			08/09/2002
	A53	2003/0077867	04/24/2003	Fitzgerald			07/16/2001
	A54	2003/0089901	05/15/2003	Fitzgerald			07/16/2001
	A55	09/906,545	07/16/2001	Fitzgerald			
	A56	09/906,200	07/16/2001	Fitzgerald			
	A57	10/164,665	06/07/2002	Currie et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
EXAMINER	J. NGUYEN	
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	APPLICANTS:	Lee et al. 10/788741
	SERIAL NO.:	Not yet assigned
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	GROUP:	Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A58	4,920,076	04/24/1990	Holland et al.			
TN	A59	5,312,766	05/17/1994	Aronowitz et al.			
TN	A60	5,327,375	07/05/1994	Harari			

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TN	B25	0 844 651 A1	05/27/1998	EP				NO	YES

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
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TN	C71	Srolovitz, "On the Stability of Surfaces of Stressed Solids," <u>Acta metall.</u> , Vol. 37, No. 2 (1989) pp. 621-625.
TN	C72	Cullis et al, "The characteristics of strain-modulated surface undulations formed upon epitaxial Si _{1-x} Ge _x alloy layers on Si," <u>Journal of Crystal Growth</u> , Vol 123 (1992) pp. 333-343.

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TN	A61	5,461,243	10/24/1995	Ek et al.		

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TN	C73	Wolf et al., "Silicon Processing for the VLSI Era, Volume 1: Process Technology" (1986) pp. 201.

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	FILING DATE: <i>2-27-04</i> Herewith GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>TN</i>	A62	5,847,419	12/08/1998	Imai et al.			

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EXAM INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

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EXAMINER	<i>T. N. N. N. N.</i>	DATE CONSIDERED	<i>6/22/06</i>
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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-012DV APPLICANTS: Lee et al. SERIAL NO.: Not yet assigned 10/788741 FILING DATE: Herewith 2-27-04 GROUP: Not yet assigned				
U.S. PATENT DOCUMENTS								
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
TN	A63	5,847,419	12/08/1998	Imai et al.				
TN	A64	6,593,191	07/15/2003	Fitzgerald			05/16/2001	
TN	A65	6,600,170	07/29/2003	Xiang			12/17/2001	
FOREIGN PATENT DOCUMENTS								
EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.								
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
TN	C73	International Search Report for PCT/US03/17275, dated October 14, 2003.						
EXAMINER T. NGUYEN				DATE CONSIDERED 6/22/06				

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	GROUP:	Not yet assigned

U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A66	5,155,571	10/13/1992	Wang et al.			
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